



AMBTA92Q

300V PNP SMALL SIGNAL TRANSISTOR IN SOT23

Description

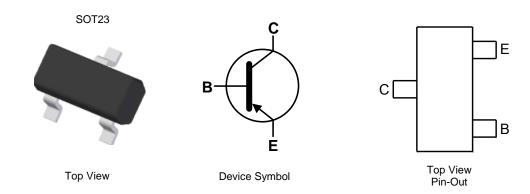
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

- BV_{CEO} > -300V
- Ideal for Medium Power Amplification and Switching
- Complementary NPN Type: MMBTA42Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: SOT23 •
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208@3
- Weight: 0.008 grams (Approximate)



Ordering Information (Notes 4 & 5)

| Part Nun | nber | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity Per Reel | | |
|--------------|--|------------|---------|--------------------|-----------------|-------------------|--|--|
| AMBTA92Q-7 | | Automotive | 2G2 | 7 | 8 | 3,000 | | |
| Notes: 1. No | Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. | | | | | | | |

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

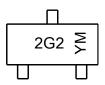
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





2G2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Kev

| Year | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code | E | F | G | Н | I | J | K | L | М | Ν | 0 | Р |
| | | | | | | | | | | | | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | -300 | V |
| Collector-Emitter Voltage | V _{CEO} | -300 | V |
| Emitter-Base Voltage | V _{EBO} | -5.0 | V |
| Collector Current | lc | -500 | mA |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|----------|----------------------|-------------|------|
| Power Dissipation | (Note 6) | PD | 300 | mW |
| Thermal Resistance, Junction to Ambient (Note 6) | | R _{0JA} | 417 | °C/W |
| Operating and Storage Temperature Range | | TJ, T _{STG} | -55 to +150 | °C |

ESD Ratings (Note 7)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | ЗA |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | С |

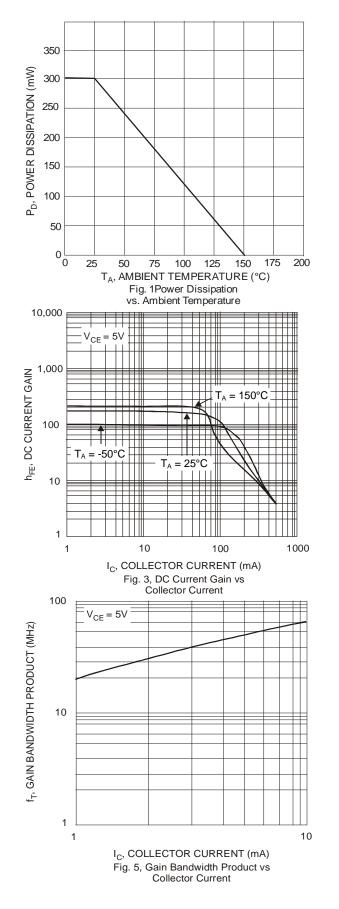
Notes: 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state. 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

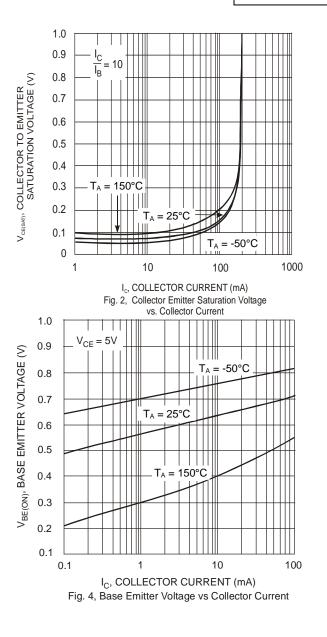
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Max | Unit | Test Condition |
|--------------------------------------|----------------------|------|------|------|---|
| OFF CHARACTERISTICS (Note 8) | | | • | | |
| Collector-Base Breakdown Voltage | BV _{CBO} | -300 | | V | I _C = -100μA |
| Collector-Emitter Breakdown Voltage | | -300 | | V | I _C = -1.0mA |
| Emitter-Base Breakdown Voltage | | -5.0 | | V | I _E = -100μA |
| Collector Cut-Off Current | I _{CBO} | _ | -250 | nA | V _{CB} = -200V |
| Emitter Cut-Off Current | I _{EBO} | | -100 | nA | V _{EB} = -3.0V |
| ON CHARACTERISTICS (Note 8) | | | | | |
| | | 25 | _ | | $I_{C} = -1.0 \text{mA}, V_{CE} = -10 \text{V}$ |
| DC Current Gain | h _{FE} | 40 | | | $I_{C} = -10 \text{mA}, V_{CE} = -10 \text{V}$ |
| | | 25 | | | $I_{C} = -30 \text{mA}, V_{CE} = -10 \text{V}$ |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | _ | -0.5 | V | $I_{C} = -20mA$, $I_{B} = -2.0mA$ |
| Base-Emitter Saturation Voltage | V _{BE(SAT)} | _ | -0.9 | V | $I_{C} = -20mA$, $I_{B} = -2.0mA$ |
| SMALL SIGNAL CHARACTERISTICS | | | | | |
| Output Capacitance | Cobo | _ | 6.0 | pF | $V_{CB} = -20V, f = 1.0MHz, I_E = 0$ |
| Current Gain-Bandwidth Product | f _T | 50 | — | MHz | $V_{CE} = -20V, I_C = -10mA, f = 100MHz$ |

8. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%. Note:



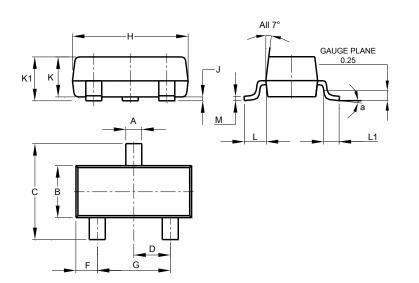






Package Outline Dimensions

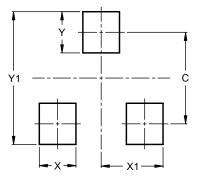
Please see http://www.diodes.com/package-outlines.html for the latest version.



| | SOT23 | | | | | | |
|-----|--------|----------|-------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| Α | 0.37 | 0.51 | 0.40 | | | | |
| в | 1.20 | 1.40 | 1.30 | | | | |
| C | 2.30 | 2.50 | 2.40 | | | | |
| D | 0.89 | 1.03 | 0.915 | | | | |
| F | 0.45 | 0.60 | 0.535 | | | | |
| G | 1.78 | 2.05 | 1.83 | | | | |
| Н | 2.80 | 3.00 | 2.90 | | | | |
| J | 0.013 | 0.10 | 0.05 | | | | |
| K | 0.890 | 1.00 | 0.975 | | | | |
| K1 | 0.903 | 1.10 | 1.025 | | | | |
| L | 0.45 | 0.61 | 0.55 | | | | |
| L1 | 0.25 | 0.55 | 0.40 | | | | |
| М | 0.085 | 0.150 | 0.110 | | | | |
| а | 0° | 8° | | | | | |
| All | Dimens | sions in | mm | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

SOT23

| Dimensions | Value (in mm) | | | |
|------------|---------------|--|--|--|
| С | 2.0 | | | |
| Х | 0.8 | | | |
| X1 | 1.35 | | | |
| Y | 0.9 | | | |
| Y1 | 2.9 | | | |

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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